

Date: 18-Jun-2024

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NXP SEMICONDUCTORS

HIGH TECH CAMPUS 60, 5656AG EINDHOVEN, THE NETHERLANDS

The following sample(s) was/were submitted and identified by the applicant as:

No.: EKR24600527

Sample Submitted By : NXP SEMICONDUCTORS NETHERLANDS B.V.

Sample Name : CHANDLER GOLD BUMPED WAFER

Sample Receiving Date

: 11-Jun-2024

Testing Period : 11-Jun-2024 to 18-Jun-2024

Test Requested : (1) As specified by client, with reference to RoHS 2011/65/EU Annex II and amending

Directive (EU) 2015/863 to determine Cadmium, Lead, Mercury, Cr(VI), PBBs, PBDEs,

DBP, BBP, DEHP, DIBP contents in the submitted sample(s).

(2) Please refer to next pages for the other item(s).

Test Results

Please refer to following pages.

Conclusion : (1) Based on the performed tests on submitted sample(s), the test results of Cadmium,

Lead, Mercury, Cr(VI), PBBs, PBDEs, DBP, BBP, DEHP, DIBP comply with the limits as set by RoHS Directive (EU) 2015/863 amending Annex II to Directive 2011/65/EU.

Ray Chang, Ph.D./Departmen Manager Signed for and on behalf SGS TAIWAN LTD.
Chemical Laboratory-Kaohsiung

CHECK REPORT

PIN CODF: 116D671



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Test Part Description

No.1 : WAFER

Test Result(s)

Test Item(s)	Method	Unit	MDL	Result	Limit
				No.1	
Cadmium (Cd)	With reference to IEC 62321-5: 2013,	mg/kg	2	n.d.	100
Lead (Pb)	analysis was performed by ICP-OES.	mg/kg	2	n.d.	1000
Mercury (Hg)	With reference to IEC 62321-4: 2013+	mg/kg	2	n.d.	1000
	AMD1: 2017, analysis was performed by ICP-OES.				
Hexavalent Chromium Cr(VI)	With reference to IEC 62321-7-2: 2017, analysis was performed by UV-VIS.	mg/kg	8	n.d.	1000
Monobromobiphenyl		mg/kg	5	n.d.	-
Dibromobiphenyl		mg/kg	5	n.d.	-
Tribromobiphenyl		mg/kg	5	n.d.	-
Tetrabromobiphenyl		mg/kg	5	n.d.	-
Pentabromobiphenyl		mg/kg	5	n.d.	-
Hexabromobiphenyl		mg/kg	5	n.d.	-
Heptabromobiphenyl		mg/kg	5	n.d.	-
Octabromobiphenyl		mg/kg	5	n.d.	-
Nonabromobiphenyl		mg/kg	5	n.d.	ı
Decabromobiphenyl		mg/kg	5	n.d.	-
Sum of PBBs	With reference to IEC 62321-6: 2015,	mg/kg	1	n.d.	1000
Monobromodiphenyl ether	analysis was performed by GC/MS.	mg/kg	5	n.d.	-
Dibromodiphenyl ether		mg/kg	5	n.d.	-
Tribromodiphenyl ether		mg/kg	5	n.d.	ı
Tetrabromodiphenyl ether		mg/kg	5	n.d.	ı
Pentabromodiphenyl ether		mg/kg	5	n.d.	ı
Hexabromodiphenyl ether		mg/kg	5	n.d.	-
Heptabromodiphenyl ether		mg/kg	5	n.d.	-
Octabromodiphenyl ether		mg/kg	5	n.d.	-
Nonabromodiphenyl ether		mg/kg	5	n.d.	-
Decabromodiphenyl ether		mg/kg	5	n.d.	=
Sum of PBDEs		mg/kg	-	n.d.	1000



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Method	Unit	MDL	Result	Limit
With reference to IEC (2221 0: 2017	100 m /l cc	Γ0		1000
·	mg/kg	50	n.a.	1000
	m a /l : a:	ΓΛ	n d	1000
,	mg/kg	50	n.a.	1000
·				1000
•	mg/kg	50	n.a.	1000
·				1000
·	mg/kg	50	n.d.	1000
		- FO		
·	mg/kg	50	n.d.	-
,	mg/kg	50	n.d.	-
3 1				
•	mg/kg	50	n.d.	-
,	mg/kg	50	n.d.	-
3				
· ·	mg/kg	2	n.d.	-
, ,				
•	mg/kg	2	n.d.	-
analysis was performed by ICP-OES.				
With reference to US EPA 3052: 1996,	mg/kg	2	n.d.	-
analysis was performed by ICP-OES.				
With reference to BS EN 14582: 2016,	mg/kg	50	n.d.	-
analysis was performed by IC.				
With reference to BS EN 14582: 2016,	mg/kg	50	n.d.	-
analysis was performed by IC.				
With reference to BS EN 14582: 2016,	mg/kg	50	n.d.	-
analysis was performed by IC.				
With reference to BS EN 14582: 2016,	mg/kg	50	n.d.	-
analysis was performed by IC.				
	analysis was performed by ICP-OES. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016,	analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to US EPA 3052: 1996, analysis was performed by ICP-OES. With reference to US EPA 3052: 1996, analysis was performed by ICP-OES. With reference to US EPA 3052: 1996, analysis was performed by ICP-OES. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC.	analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to US EPA 3052: 1996, analysis was performed by ICP-OES. With reference to US EPA 3052: 1996, analysis was performed by ICP-OES. With reference to US EPA 3052: 1996, analysis was performed by ICP-OES. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC.	analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to IEC 62321-8: 2017, analysis was performed by GC/MS. With reference to UEC 62321-8: 2017, analysis was performed by GC/MS. With reference to UEC 62321-8: 2017, analysis was performed by ICP-OES. With reference to US EPA 3052: 1996, analysis was performed by ICP-OES. With reference to US EPA 3052: 1996, analysis was performed by ICP-OES. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC. With reference to BS EN 14582: 2016, analysis was performed by IC.



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Note:

- 1. mg/kg = ppm; 0.1wt% = 0.1% = 1000ppm
- 2. MDL = Method Detection Limit
- 3. n.d. = Not Detected (Less than MDL)
- 4. "-" = Not Regulated
- 5. Unless otherwise stated, the decision rule for conformity reporting is based on Binary Statement for Simple Acceptance Rule (w=0) stated in ILAC-G8:09/2019. According to this rule, the judgement of conformity is based on the comparing test results with limits.

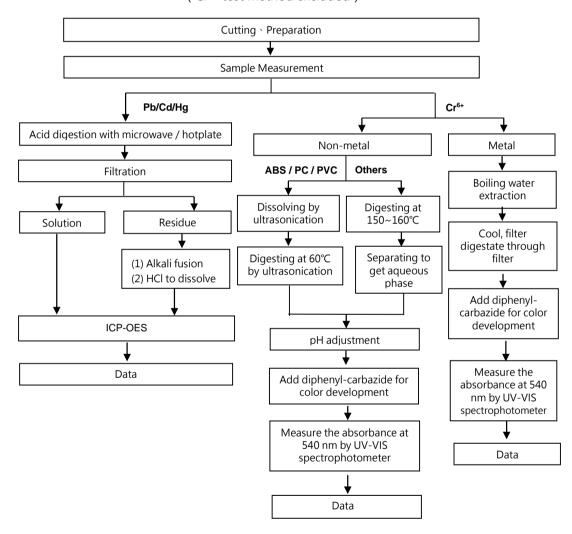


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Analytical flow chart of Heavy Metal

These samples were dissolved totally by pre-conditioning method according to below flow chart. (Cr^{6+} test method excluded)

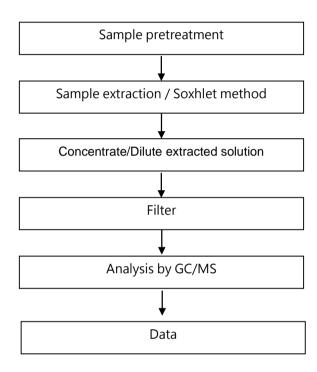




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PBB/PBDE analytical FLOW CHART



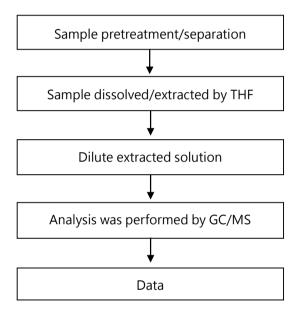


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Analytical flow chart of phthalate content

【Test method: IEC 62321-8】





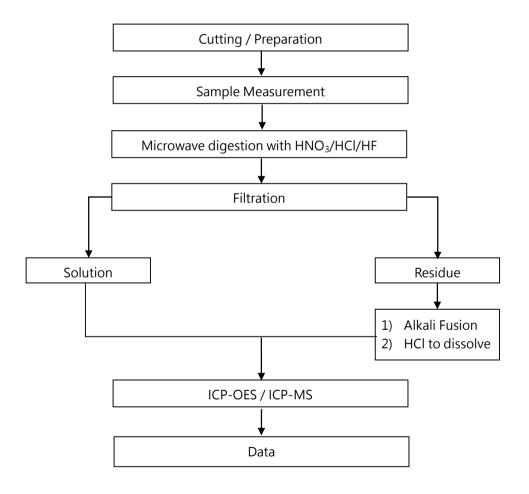
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Analytical flow chart of Elements (Heavy metal included)

These samples were dissolved totally by pre-conditioning method according to below flow chart.

【Reference method: US EPA 3051 \ US EPA 3052】



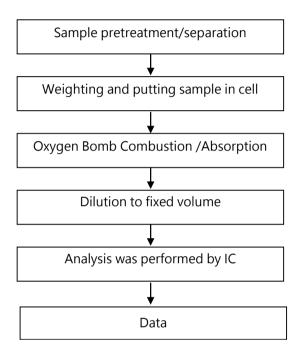
* US EPA 3051 method does not add HF.



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Analytical flow chart of Halogen



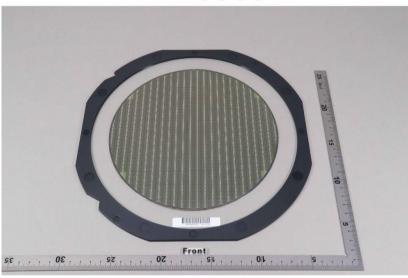


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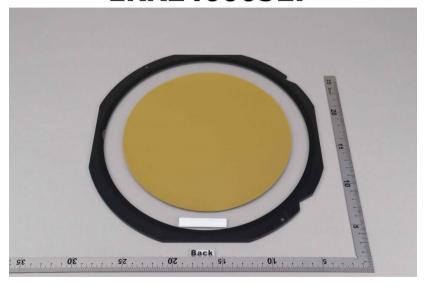
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* The tested sample / part is marked by an arrow if it's shown on the photo. *

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** End of Report **

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